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Evaluation of Energy and Density of States of Two Dimensional Quantum Structure (Quantum Well)

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Authors' contributions

This work was carried out in collaboration between all authors. Author JI designed the study, performed the statistical analysis, wrote the protocol and first draft of the manuscript. Authors IJA, MYM and NO managed the analyses of the study and the literature searches. All authors read and approved the final manuscript.

Article Information

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ABSTRACT

Quantum structures (e.g. quantum wells) are a critical part of optical system designs (lasers, modulators, switches etc.). In the quantum well, the motion of the particle is quantized in one direction while the particle moves freely in other two directions. The density of state of the quantum structure is the possible number of state an excited electron can occupy per unit volume. The density of state depends on the energy at which the electron moves when excited. In this paper, the energy and density of states of two-dimensional quantum structure (quantum well) were calculated. The results obtained revealed the density of state increases with the energy but exhibited maximum and minimum peaks. Maximum peaks occurred at 4 eV and 7.5 eV while the minimum peaks occurred at 5 eV and 8 eV. These show that energy of state for quantum wells neither varies linearly nor exponentially with a density of state because of high energy level. The findings are in agreement with published literature. Some applications of quantum wells include: bioconjugates, solar cells, photovoltaic, photo and electrochromic devices etc.

Keywords: Confinement; density of state; energy of state; quantum structure; quantum well.

1. INTRODUCTION

One of the most significant nanostructures required for the design and building of nanoelectronic devices is guantum well [1]. Quantum well is referred to a semiconductor region that possesses lower energy where electrons and holes are trapped and whose properties are governed by quantum mechanics (where specific energies and band gaps are allowed). The typical nanoscale dimension of the quantum well is between 1-1000 nm [1,2]. Quantum wells are practical vital semiconductor devices used in many applications (e.g. LEDs, lasers, detectors etc.). Their optical transitions are very strong with the capability of tuning the energy. However, they also rely on optical transitions between the valence and conduction bands called inter-band transitions [3]. There are also optical transitions between the different electron levels within the quantum well called the inter-subband transitions. The inter-band and inter-subband transitions have a smaller energy gap which enables them to interact with light in the mid- to far- infrared part of the spectrum [3,4].

In quantum wells, electrons are confined in one direction and free to move only in the other two directions as seen in Fig. 1. So, the electronic energy level bands are less crowded when compared with bulk materials [5].



Fig. 1. One dimension quantization in the quantum well

A narrow band-gap material is placed between wider band-gap materials as shown in Fig. 2. The decrease of the thickness of the good layer results to decrease in the electron and hole waveforms in the quantum well by the surrounding layers [6]. The band gaps of two different semiconductors can be joined to form a hetero-junction. A potential well can be formed from the discontinuity in either the valence or conduction band. From Fig. 2, if a thin layer of a narrowerband gap material 'A' is sandwiched between two layers of a wider-bandgap material 'B', then a double hetero-junction is formed. A single quantum well can also be formed if layer 'A' is sufficiently thin for quantum properties to be exhibited.



Fig. 2. Energy band diagram of a quantum well

As a result of confinement of excitons in layers with a thickness less than the exciton Bohr diameter, the oscillator strength and binding energy of the exciton increase [6]. The excitonic states become more stable and more visible at room temperature which is an impossible phenomenon in bulk structures. It is thinner and gets smaller in all directions. The holes and the electrons are closer to each other which results to larger Coulomb binding energy, faster classical orbit time, and greater optical absorption strength. Quantum confinement allows the quantum structure to be tailored to specific incident energy levels based on particle size. Quantum-confined structure is categorized based on the conferment direction into quantum well, quantum wire and quantum dots [7]. Quantum well could be finite, infinite or superlattice. Infinite quantum well, the particle in the box exhibit tunneling penetration while in an infinite quantum well the particle is seen in the box only. Whereas, in superlattice quantum well the wells are so close that the wave-functions couple to give "minibands" [8].

dot sheet bulk 3D 2D 1D 0D g(E) g(E) g(E) g(E) Eg E E F F Eq Eg E

g(E) = Density of states

Fig. 3. Density of electron states of a semiconductor as a function of dimension

The number of states attained by a quantum system is the possible number of available states. It is given mathematically as [2]:

$$\varphi (E) = \frac{v \text{ system}}{v \text{ single-state}} x N$$
(1)

where

 $\phi(E)$ is a number of states, V_{system}is volume of the whole system (sphere, circle, line), V_{single} is volume of a single state of that system, and N is the number of atoms in the crystal. Each quantum state has unique wave function.

Density of state is the possible number of state an electron when excited can occupy per unit volume [9]. The density of state depends on the energy at which the electron moves when excited. It is the first derivative of the number of state with respect to the energy. It is given mathematically as [10].

$$g(E) = \frac{d \phi(E)}{dE}$$
(2)

where

g(E) is the density of state and ϕ is number of states.

Density of electron states in bulk, 2D, 1D and 0D semiconductor structure is shown in Fig. 3 [2, 11]. 0D structures have very well defined and quantized energy levels. The quantum confinement effect corresponding to the size of the nanostructure can be estimated via a simple effective-mass approximation model.

2. RESEARCH METHODOLOGY

2.1 Energy and Density of State of Quantum Well

In this case, a semiconductor is modelled as a quantum well (2D) with each side equal to I. The electron of mass m^* are confined in the well. Setting the potential energy (P.E) = 0, and solving the Schrodinger equation yields;

$$\nabla^{2}\Psi(\mathbf{x},\mathbf{y},\mathbf{z}) + \frac{2\mathbf{m}(\mathbf{E}-\mathbf{V})}{\hbar^{2}}\Psi(\mathbf{x},\mathbf{y},\mathbf{z}) = 0 \tag{3}$$

But for 2D,

$$\nabla^2 = \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} \tag{4}$$

Since potential energy is zero, then equation 3 becomes:

$$\frac{\partial^{2\Psi}(\mathbf{x},\mathbf{y})}{\partial \mathbf{x}^{2}} + \frac{\partial^{2\Psi}(\mathbf{x},\mathbf{y})}{\partial \mathbf{y}^{2}} + \frac{2\mathrm{mE}}{\hbar^{2}}\Psi(\mathbf{x},\mathbf{y}) = 0$$
(5)

But,

$$\frac{\partial \Psi}{\partial x} = \Psi(y)\Psi(z)\frac{d\Psi}{dx}$$
 and $\frac{\partial \Psi}{\partial y} = \Psi(x)\Psi(z)\frac{d\Psi}{dy}$ (6)

Also,

$$\frac{\partial^2 \Psi}{\partial x^2} = \Psi(y) \frac{d^2 \Psi}{dx^2} \text{ and } \frac{\partial^2 \Psi}{\partial y^2} = \Psi(x) \frac{d^2 \Psi}{dy^2}$$
(7)

Putting equations 6 and 7 into equation 5 gives:

$$\Psi(y)\frac{d^{2}\Psi(x)}{dx^{2}} + \Psi(x)\frac{d^{2}\Psi(y)}{dy^{2}} + \frac{2mE}{\hbar^{2}}\Psi(x)\Psi(y) = 0$$
(8)

Divide through equation 8 by $\Psi(x)\Psi(y)$ and Let $\frac{2mE}{\hbar^2}$ = K² then,

$$\frac{1}{\Psi(x)}\frac{d^2\Psi(x)}{dx^2} + \frac{1}{\Psi(y)}\frac{d^2\Psi(y)}{dy^2} + \frac{2mE}{\hbar^2} = 0$$
(9)

Or,

$$\frac{1}{\psi(x)}\frac{d^2\psi(x)}{dx^2} + \frac{1}{\psi(y)}\frac{d^2\psi(y)}{dy^2} + \frac{1}{\psi(z)}\frac{d^2\psi(z)}{dz^2} + K^2 = 0$$
(10)

where

K is a constant.

$$\frac{d^2\Psi(x)}{dx^2} + \frac{d^2\Psi(y)}{dy^2} + K^2\Psi(x)\Psi(y) = 0$$
 (11)

The solution to the equation 11 is given as:

$$\Psi(x) = A \sin Kx + B \cos Kx$$

 $\Psi(y) = A \sin Ky + B \cos Ky$
At the point $\Psi(x) = 0$ and $x = 0$

0=A sin (0) +B cos (0) Therefore, B=0

Hence, $\Psi(x) = A \sin Kx$

Taking the boundary conditions at $\Psi(x)=0$; x=l

$$0 = A \sin KI$$
 But $A \neq 0$

Since KI = 0 then,

 $KI = sin^{-1}(0) = n\pi$

Therefore, $K = \frac{n\pi}{1}$

Substituting back gives:

$$\begin{split} \Psi(x) &= A \sin \frac{n_x \pi x}{l} \quad \text{and} \quad K_x = \frac{n_x \pi}{l} \\ \Psi(y) &= A \sin \frac{n_y \pi y}{l} \quad \text{and} \quad K_y = \frac{n_y \pi}{l} \\ \text{Thus, } K &= K_x + K_y = \frac{n_x \pi}{l} + \frac{n_y \pi}{l} \end{split}$$

Normalizing the wave function,

$$\int \Psi(x) \Psi(x)^* = \int A^2 \sin^2 \frac{n_x \pi}{l} = 1$$

Therefore, A = $\sqrt{\frac{2}{l}}$ and

$$\Psi(x,y) = \sqrt{\frac{2}{l}} \sin \frac{n_x \pi x}{l} \sqrt{\frac{2}{l}} \sin \frac{n_y \pi y}{l}$$
(12)

Thus, the wave function of such a system is given by:

$$\Psi(\mathbf{x}, \mathbf{y}, \mathbf{z}) = \sqrt{\frac{4}{l^2}} \sin \frac{\mathbf{n}_{\mathbf{x}} \pi \mathbf{x}}{l} \sin \frac{\mathbf{n}_{\mathbf{y}} \pi \mathbf{y}}{l}$$
(13)

Using the principle of effective mass approximation,

$$\mathsf{E} = \frac{\hbar^2 \kappa^2}{2\mathrm{m}^*} \tag{14}$$

But,
$$K^2 = \frac{2m^*E}{\hbar^2} = (\frac{n\pi}{l})^2$$
 and $n = n_x^2 + n_y^2$ (15)

Substituting for K into E gives

$$E = \frac{\hbar^2 \pi^2 n^2}{2m^{*1^2}}$$
$$E = \frac{\hbar^2 \pi^2}{2m^{*1^2}} (n_x^2 + n_y^2)$$
(16)

The equation 16 is the energy of a 2-dimensional quantum well.

K-space volume for a single state = $(\frac{\pi}{a})(\frac{\pi}{a}) = \frac{\pi^2}{v} = \frac{\pi^2}{l^2}$

K-space volume for the 2-dimensional system (circle) = V circle = πR^2

But,

$$R^{2} = (n_{x}^{2} + n_{y}^{2}) = \frac{2m^{*}l^{2}E}{\hbar^{2}\pi^{2}} \text{ and } R = (\frac{2m^{*}l^{2}E}{\hbar^{2}\pi^{2}})^{1/2}$$
(17)

$$V_{\text{circle}} = \pi \ x \ (\frac{2m^*l^2 E}{\hbar^2 \pi^2})^{1/2}$$
(18)

Number of atoms for a crystal at position (0, 0) and (1/2,1/2) is = 2 x $\frac{1}{2} x \frac{1}{2}$

So,

$$\begin{split} \phi(E) &= \frac{\pi x \left(\frac{2m^{*}l^{2}E}{\hbar^{2}\pi^{2}}\right)^{1/2}}{\frac{\pi^{2}}{l^{2}}} x 2 x \frac{1}{2} x 2 = \\ \frac{\pi l^{2}}{a\pi^{2}} \left(\frac{2m^{*}l^{2}E}{\hbar^{2}\pi^{2}}\right)^{1/2} x \frac{2}{2} x \frac{1}{2} x \frac{1}{2} \\ \phi(E) &= \frac{l^{2}}{\pi} \left(\frac{2m^{*}l^{2}E}{\hbar^{2}\pi^{2}}\right)^{1/2} x \frac{1}{2} = \frac{l^{3}}{2\pi\hbar} \left(\frac{2m^{*}E}{\pi}\right)^{1/2} E^{\frac{1}{2}} \end{split}$$
(19)

The density of state is therefore given as:

$$g(E)_{2D} = \frac{d \phi(E)}{dE} = \frac{1}{2} x \frac{l^3}{2\pi\hbar} \left(\frac{2m^*E}{\pi}\right)^{\frac{1}{2}} E^{\frac{1}{2}-1} = \frac{1}{2} x \frac{\pi}{\pi\hbar} \left(\frac{2m^*E}{\pi}\right)^{\frac{1}{2}} E^{\frac{1}{2}-1}$$
(20)

Thus, the density of state per unit volume V is:

$$g(E)_{2D} = \frac{\frac{1}{2} x \frac{l^3}{\pi \hbar} (\frac{2m^*E}{\pi})^{1/2} E^{-\frac{1}{2}}}{V} = \frac{\frac{1}{2} x \frac{l^3}{\pi \hbar} (\frac{2m^*E}{\pi})^{1/2} E^{-\frac{1}{2}}}{l^3}$$
$$g(E)_{2D} = \frac{1}{2\pi} (\frac{2m^*}{\hbar^2})^{\frac{1}{2}} E^{-\frac{1}{2}}$$
(21)

Equation 21 gives the density of state for a 2dimensional infinite potential well.

2.2 Data Analysis

The following parameters were used in the calculations of the energy and density of states of quantum dots in one dimension and result tabulated in Table 1.

$$\hbar = \frac{h}{2\pi} = 1.054 \text{ x } 10^{-34} \text{ J. S}$$

 $\pi = 22/7 = 3.142$

- L = dimension of well and line assumed =10 A^0 = 10 x 10⁻¹⁰ m
- m^* = mass of the electron = 9.11 x 10⁻³¹ kg
- E = charge of electron = $1.6 \times 10^{-19} C$

3. RESULTS AND DISCUSSION

3.1 Results

The results for the energy and density of states of quantum dots in one dimension as calculated are given in Table 1.

3.2 Discussion

From Fig. 4 and Table 1, it shows that the density of state increases with the energy but exhibit maximum and minimum peaks. Maximum peaks occurred at 4eV and 7.5eV while the minimum peaks occurred at 5eV and 8eV. The energy continues to increase up to 12eV, for the first different levels investigated. These show that energy of state for quantum wells neither varies linearly nor exponentially with a density of state because of high energy level. Also, this is a proof that density of state of quantum wells depends on other factors apart from energy. The findings are in agreement with published literature. The results obtained in this work may slightly differ from real life situations because of the following reasons:

- I. In the calculation, the electronic mass of the electron was used throughout and not the effective mass of the electron, which varies in the reciprocal space lattice of the solid.
- II. The dimension of the well was kept constant at a value of 10 A⁰ irrespective of the dimension under consideration. Changes in the dimension of the box will certainly cause a change in the energy level and hence the density of state of the system studied.

Energy levels	Energy (Joules)	Energy (eV)	Density of	Density of
$n_{x_i} n_{y_i}$			States (m ⁻³ J ⁻¹)	States (m ⁻³ eV ⁻¹)
1, 1	1.204x10 ⁻¹⁹	0.75250	5.873x 10 ²⁷	2.349x 10 ¹⁸
1, 2	3.0100x10 ⁻¹⁹	1.88125	3.7147x 10 ²⁷	1.48587x10 ¹⁸
1, 3	6.0200x 10 ⁻¹⁹	3.76250	2.6267x 10 ²⁷	1.051x 10 ¹⁸
1, 4	1.0234x10 ⁻¹⁸	6.39625	2.0146x 10 ²⁷	8.0583x 10 ¹⁷
2, 2	4.8160x10 ⁻¹⁹	3.01000	2.939x 10 ²⁷	1.1747x 10 ¹⁸
2, 3	7.8260x10 ⁻¹⁹	4.89125	2.3040x 10 ²⁷	9.215x 10 ¹⁷
2, 4	1.2040x10 ⁻¹⁸	7.52500	1.857x 10 ²⁷	4.429x 10 ¹⁷
3, 3	1.0836x10 ⁻¹⁸	6.77250	1.9580x 10 ²⁷	7.831x 10 ¹⁷
3, 4	1.5050 x10 ⁻¹⁸	9.40625	1.6610x 10 ²⁷	6.645x 10 ¹⁷
4, 4	1.9264x10 ⁻¹⁸	12.0400	1.4680x 10 ²⁷	5.873x 10 ¹⁷
5, 1	1.5652x10 ⁻¹⁸	9.78250	1.6290x 10 ²⁷	6.516x 10 ¹⁷
5, 2	1.7458x10 ^{⁻18}	10.91125	1.5420x 10 ²⁷	6.1697x 10 ¹⁷
5, 3	2.0468x10 ⁻¹⁸	12.79250	1.4250x 10 ²⁷	5.698x 10 ¹⁷
5, 4	2.4682x10 ⁻¹⁸	15.42625	1.2970x 10 ²⁷	5.189x 10 ¹⁷
5, 5	3.0100x10 ⁻¹⁸	18.81250	1.1750x 10 ²⁷	4.699x 10 ¹⁷
6, 1	2.2270x10 ⁻¹⁸	13.92125	1.3660x 10 ²⁷	5.462x 10 ¹⁷
6, 2	2.4080x10 ⁻¹⁸	15.05000	1.31330x10 ²⁷	5.253x 10 ¹⁷
6, 3	2.7090x 10 ⁻¹⁸	16.93125	1.238x 10 ²⁷	4.9529x 10 ¹⁷
6, 4	3.1300 x10 ⁻¹⁸	19.56500	1.1520x 10 ²⁷	4.6075x 10 ¹⁷
6, 5	3.6722x10 ⁻¹⁸	22.95125	1.0635x 10 ²⁷	4.254x 10 ¹⁷
6, 6	4.3344 x10 ⁻¹⁸	27.09000	9.789x 10 ²⁶	3.916x 10 ¹⁷



Fig. 4. Variation density of state with energy for a 2D quantum well

4. CONCLUSION

The assessment of energy and density of states of the quantum well has a tremendous impact in nano-technology which may revolutionize technology. However, a clear understanding of energy and density of states of quantum wells is necessary for it. In this paper, the energy and density of states for a quantum well in two dimensions were calculated and analyzed. The result showed maximum and minimum peaks for the relationship between energy and density of states of quantum well-indicating non-linearity of variations.

COMPETING INTERESTS

Authors have declared that no competing interests exist.

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